

# Atomic Layer Deposition of Aluminum, Hafnium and Zirconium Oxyfluoride

## Films with Tunable Stoichiometry

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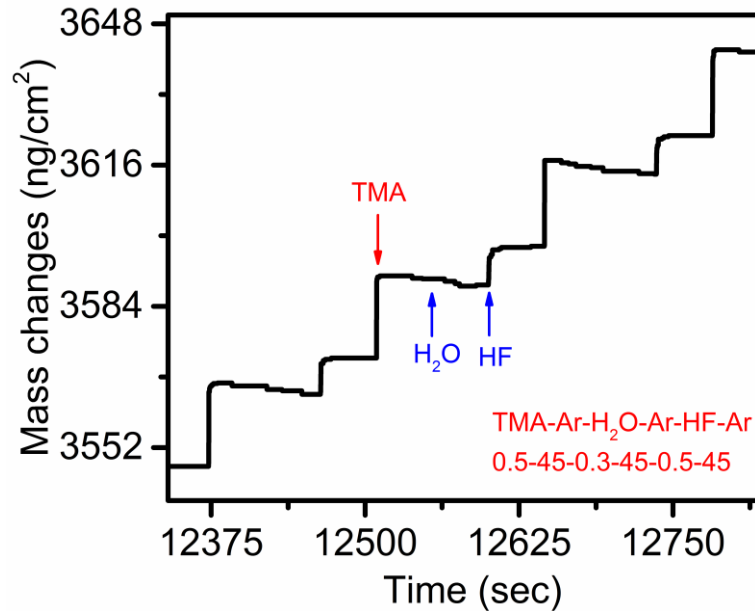


Figure 1: Mass changes recorded by in situ QCM during AlO<sub>x</sub>F<sub>y</sub> growth by the halide-exchange method at 150°C. The sequential exposure of TMA, H<sub>2</sub>O and HF yielded an average mass gain per supercycle of 24-25 ng/cm<sup>2</sup>.

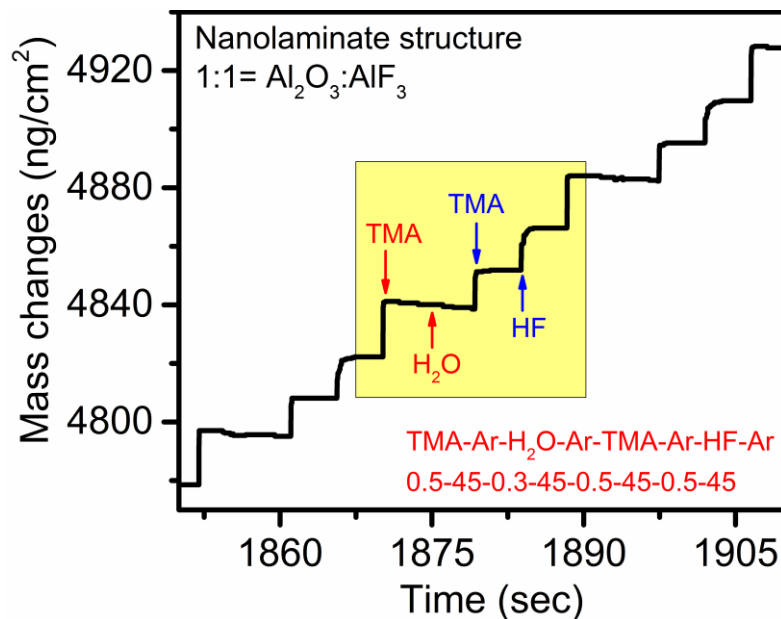


Figure 2: Mass changes recorded by in situ QCM during AlO<sub>x</sub>F<sub>y</sub> growth by the nanolaminate method at 150°C. The sequential exposure of TMA, H<sub>2</sub>O and TMA, HF yielded an average mass gain per supercycle of 60-61 ng/cm<sup>2</sup>.